





O P P 2 Q R S T U V W X

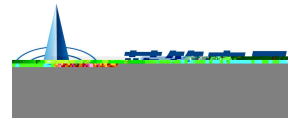
silicon PNP transistor in a SOT-363 Plastic Package.

$Y_{FE} Z [ \quad_{CE(sat)} X C D \setminus ] X$

High DC Current Gain, Low Collector to Emitter Saturation Voltage. HF Product.

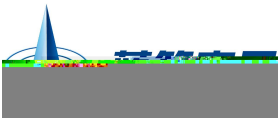
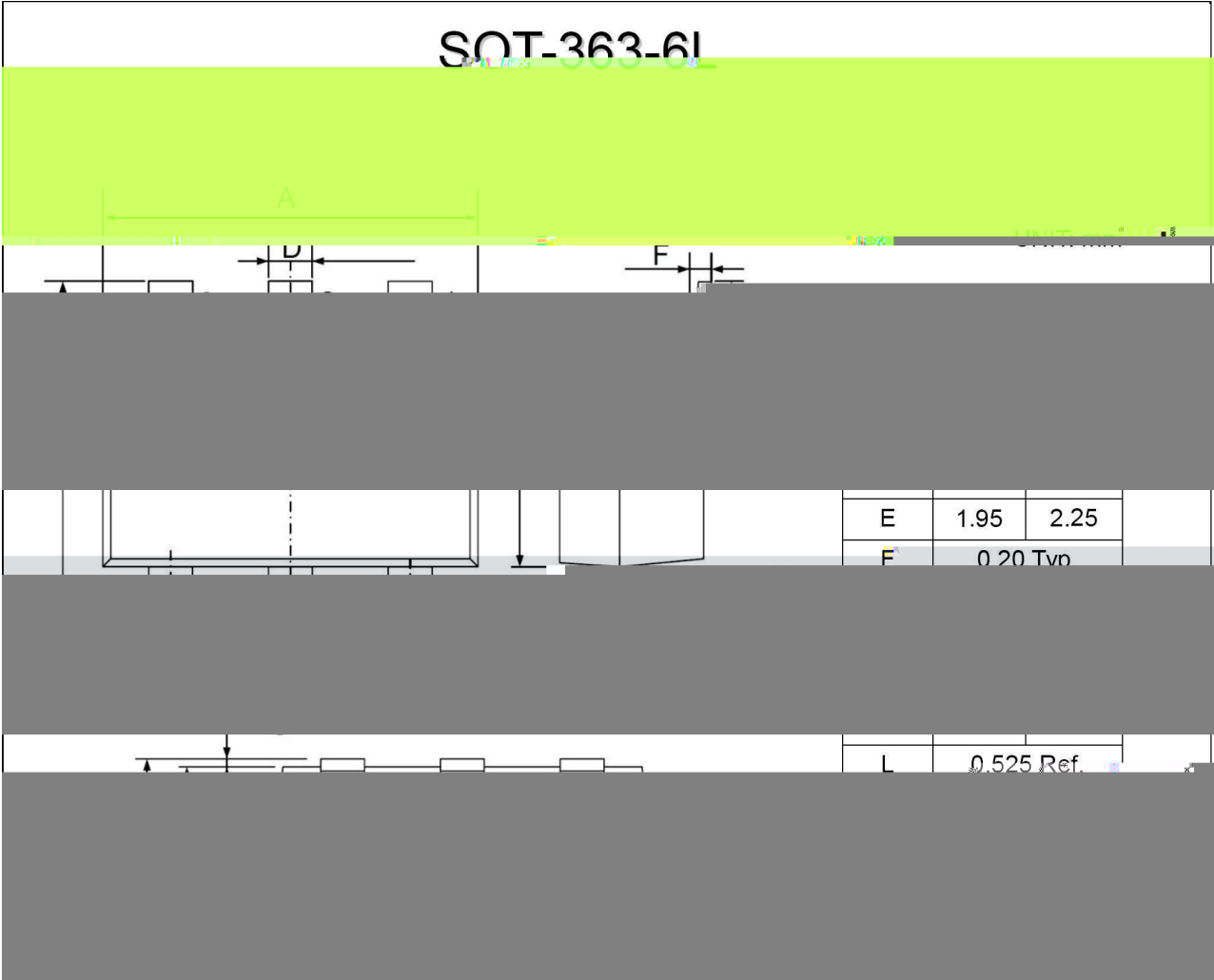
$\wedge \_ \backslash a b c ) d e X$

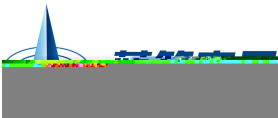
General purpose amplifier and switching.



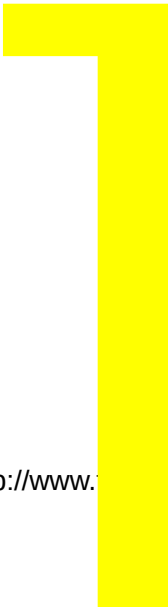
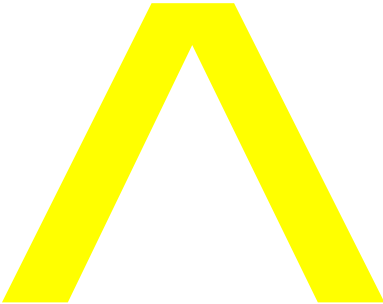
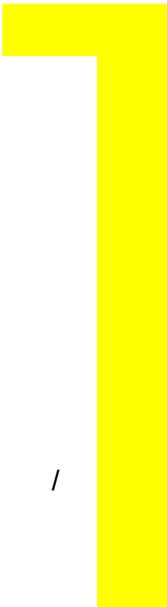
| g h<br>Parameter             | i j<br>Symbol | h k<br>Rating | l m<br>Unit |
|------------------------------|---------------|---------------|-------------|
| Collector to Base Voltage    | $V_{CBO}$     | -40           | V           |
| Collector to Emitter Voltage | $V_{CEO}$     | -40           | V           |
| Emitter to Base Voltage      | $V_{EBO}$     | -5.0          | V           |
| Collector Current            | $I_C$         | -200          | mA          |

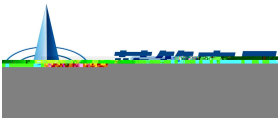






v w f  
● f      x y 1 z {  
A2 f      x u j | '  
\*\*\*:      x } \ ~ j | ' Z    } \ ~ j i ¢





Temperature Profile for IR Reflow Soldering(Pb-Free)

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|  |
|  |
|  |
|  |
|  |
|  |

- 1

150 180

60 90sec;
- 2

245±5

5±0.5sec;
- 3

2 10

/sec.
- Note:

1.Preheating:150~180 , Time:60~90sec.

2.Peak Temp.:245±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

260±5

10±1 sec.

Temp.:260±5℃

Time:10±1 sec

/ REEL

Package Type

封装形式

Units 包装数量